



# IRFP250

## N-CHANNEL 200V - 0.073Ω - 33A TO-247

### PowerMesh™II MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
IRFP250	200V	< 0.085Ω	33 A

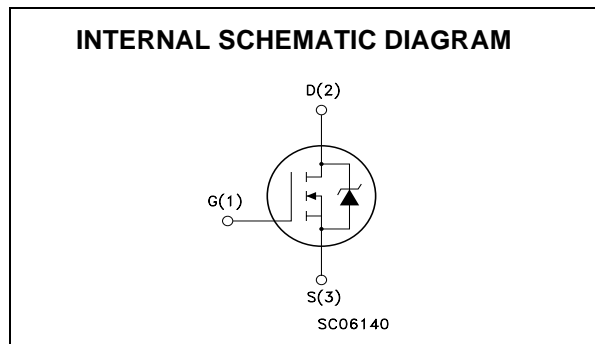
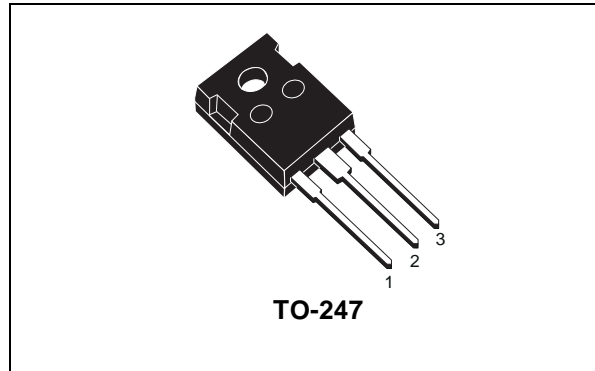
- TYPICAL R<sub>DS(on)</sub> = 0.073Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

#### DESCRIPTION

The PowerMESH™II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron\*area figure of merit while keeping the device at the leading edge for what concerns switching speed, gate charge and ruggedness.

#### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- UNINTERRUPTIBLE POWER SUPPLIES (UPS)
- DC-AC CONVERTERS FOR TELECOM, INDUSTRIAL, AND LIGHTING EQUIPMENT



#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	200	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	200	V
V <sub>GS</sub>	Gate- source Voltage	±20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	33	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	20	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	132	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	180	W
	Derating Factor	1.44	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	5	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(\*)Pulse width limited by safe operating area

(1)I<sub>SD</sub> ≤ 33A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

## IRFP250

### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	0.66	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	30	°C/W
Rthc-sink	Thermal Resistance Case-sink Typ	0.1	°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose	300	°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	33	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	600	mJ

### ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED) OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	200			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±30V			±100	nA

### ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 16A		0.073	0.085	Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , V <sub>GS</sub> = 10V	33			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> , I <sub>D</sub> = 16A	10	25		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		2850		pF
C <sub>oss</sub>	Output Capacitance			420		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			120		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 100V, I_D = 16A$ $R_G = 4.7\Omega, V_{GS} = 10V$		25		ns
$t_r$	Rise Time	(see test circuit, Figure 3)		50		ns
$Q_g$	Total Gate Charge	$V_{DD} = 160V, I_D = 33A,$ $V_{GS} = 10V, R_G = 4.7\Omega$		117	158	nC
$Q_{gs}$	Gate-Source Charge			15		nC
$Q_{gd}$	Gate-Drain Charge			50		nC

**SWITCHING OFF**

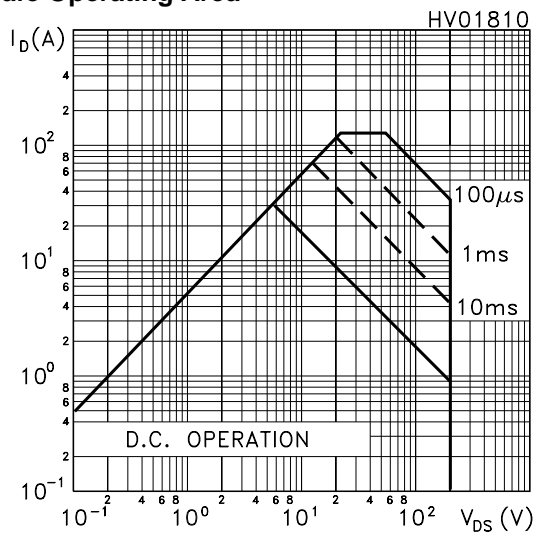
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 160V, I_D = 16A,$ $R_G = 4.7\Omega, V_{GS} = 10V$		60		ns
$t_f$	Fall Time	(see test circuit, Figure 5)		40		ns
$t_c$	Cross-over Time			100		ns

**SOURCE DRAIN DIODE**

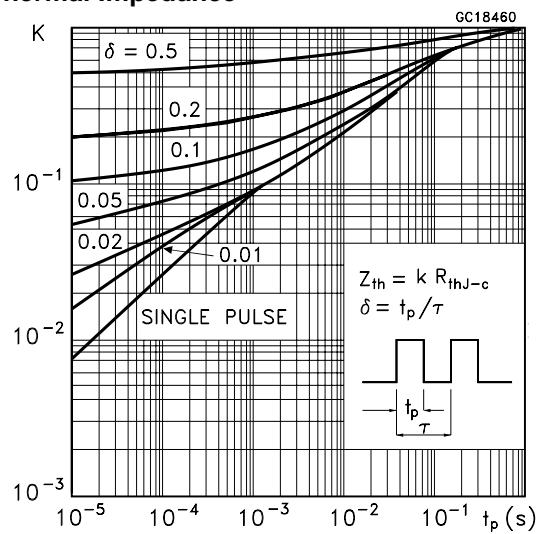
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				33	A
$I_{SDM} (2)$	Source-drain Current (pulsed)				132	A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 33A, V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 33A, di/dt = 100A/\mu s,$ $V_{DD} = 100V, T_j = 150^\circ C$		370		ns
$Q_{rr}$	Reverse Recovery Charge	(see test circuit, Figure 5)		5.4		$\mu C$
$I_{RRM}$	Reverse Recovery Current			29		A

Note: 1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

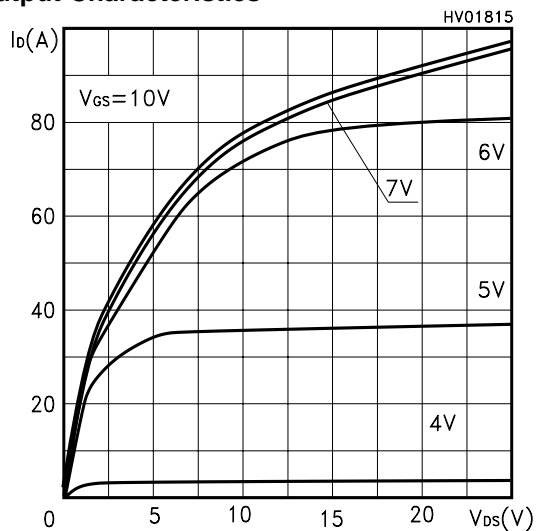
**Safe Operating Area**



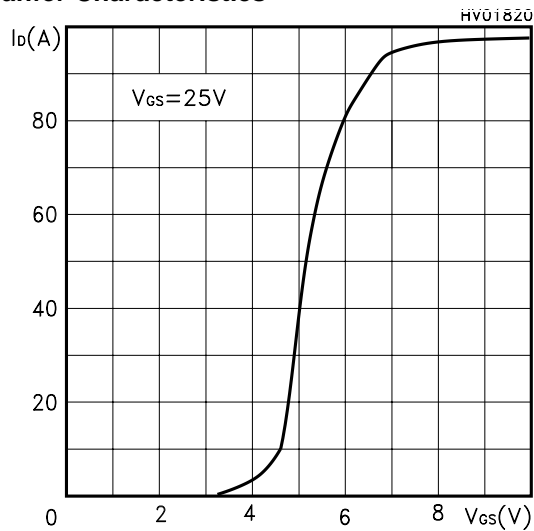
**Thermal Impedance**



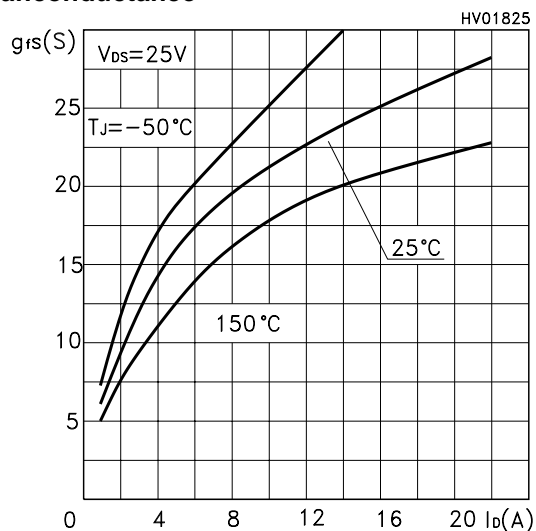
Output Characteristics



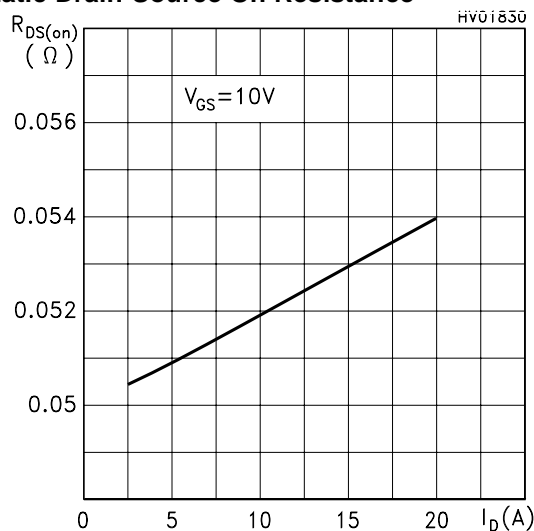
Transfer Characteristics



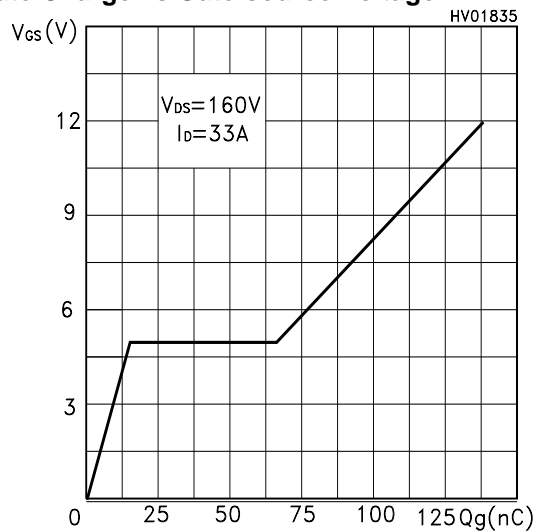
Transconductance



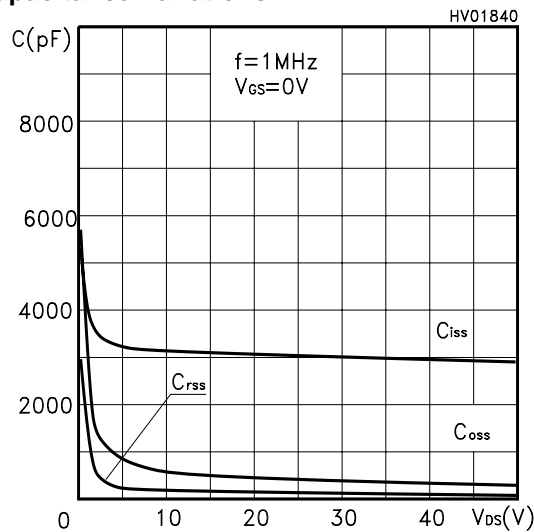
Static Drain-Source On Resistance



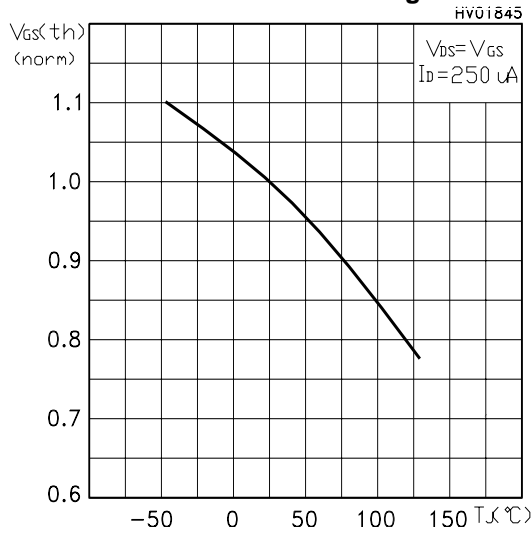
Gate Charge vs Gate-source Voltage



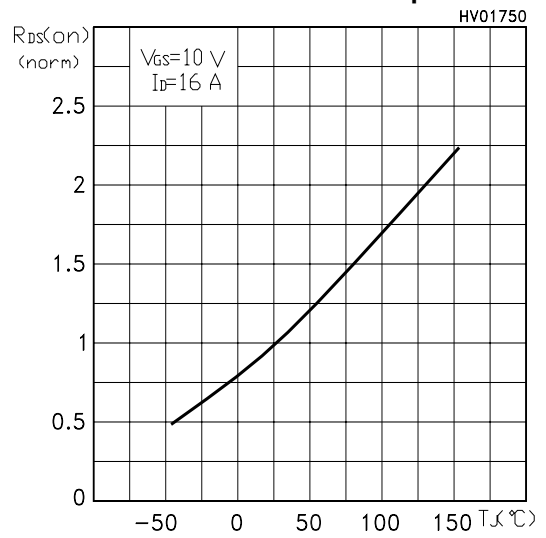
Capacitance Variations



**Normalized Gate Threshold Voltage vs Temp.**



**Normalized On Resistance vs Temperature**



**Source-drain Diode Forward Characteristics**

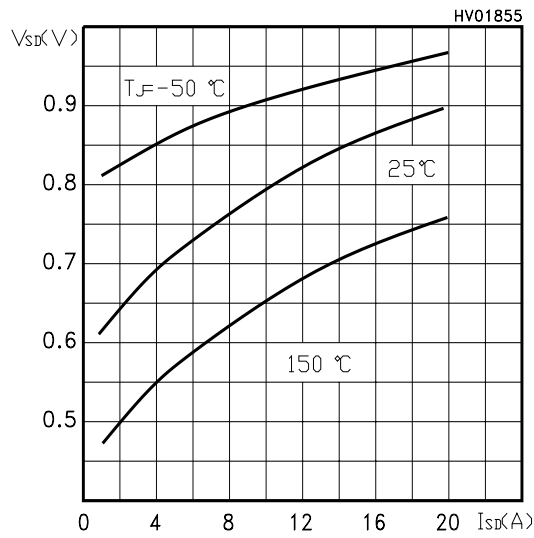


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform

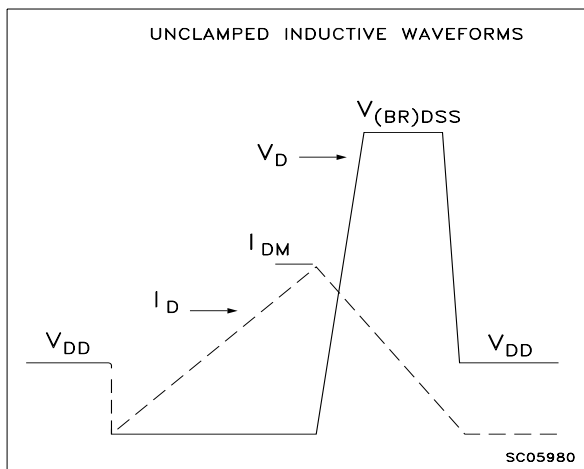


Fig. 3: Switching Times Test Circuit For Resistive Load



Fig. 4: Gate Charge test Circuit

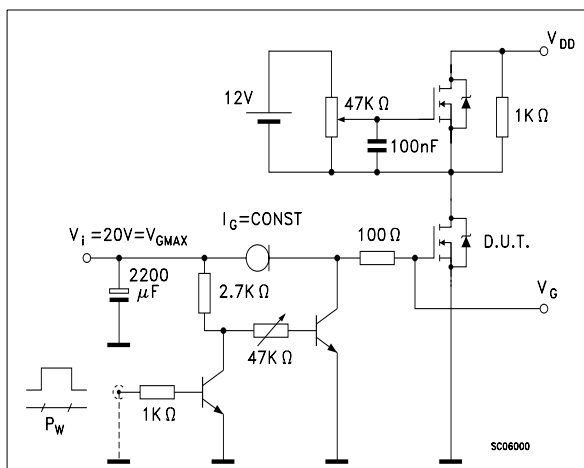
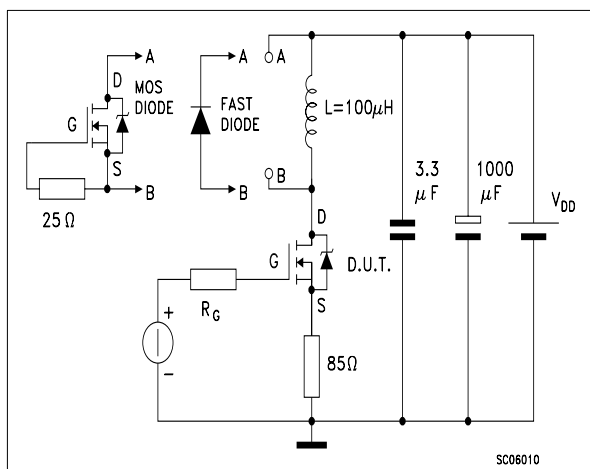
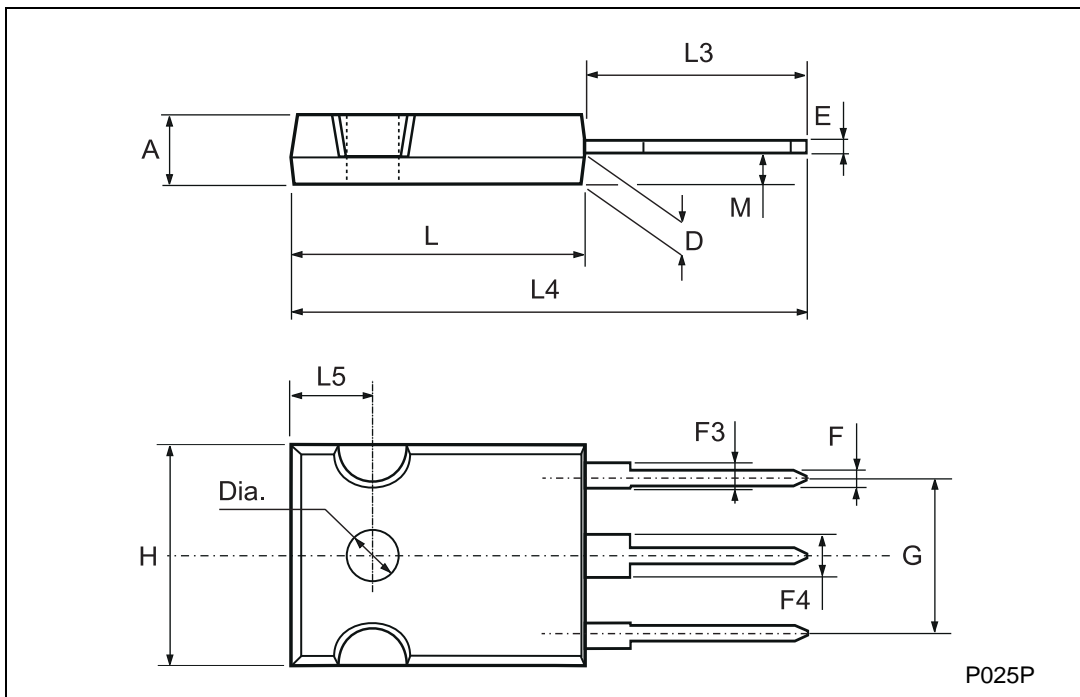


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



**TO-247 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118



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